2N5400



2N5400



PNP General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring high voltages.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	120	V
V _{CBO}	Collector-Base Voltage	130	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	600	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		2N5400	
P _D	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

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PNP General Purpose Amplifier (continued)

Symbol	Parameter	Test Conditions	Min	Мах	Units
OFF CHA		· · · ·		•	
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 1.0$ mA, $I_{\rm B} = 0$	120		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \ \mu \text{A}, \ I_{\rm E} = 0$	130		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10 \ \mu A, \ I_{\rm C} = 0$	5.0		V
I _{CBO}	Collector Cutoff Current	$V_{CB} = 100 \text{ V}, I_E = 0$ $V_{CB} = 100 \text{ V}, I_E = 0, T_A = 100 ^{\circ}\text{C}$		100 100	nA μA
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 3.0 \text{ V}, I_{C} = 0$		50	nA
h _{FE}	DC Current Gain	$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$	30 40	180	
h _{FE}	DC Current Gain	$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$	30		
h _{FE}	DC Current Gain	$V_{CE} = 5.0 \text{ V}, I_{C} = 10 \text{ mA}$	30 40 40	180	
	DC Current Gain Collector-Emitter Saturation Voltage		40	180 0.2	V
		$V_{CE} = 5.0 \text{ V}, I_C = 10 \text{ mA}$ $V_{CE} = 5.0 \text{ V}, I_C = 50 \text{ mA}$	40		V
V _{CE(sat)}			40	0.2 0.5 1.0	V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$V_{CE} = 5.0 \text{ V}, I_{C} = 10 \text{ mA}$ $V_{CE} = 5.0 \text{ V}, I_{C} = 50 \text{ mA}$ $I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$ $I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA}$	40	0.2	V
V _{CE(sat)} V _{BE(sat)} SMALL S	Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage	$V_{CE} = 5.0 \text{ V}, I_C = 10 \text{ mA}$ $V_{CE} = 5.0 \text{ V}, I_C = 50 \text{ mA}$ $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$ $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$	40	0.2 0.5 1.0 1.0	V V V
V _{CE(sat)} V _{BE(sat)} SMALL S C _{ob}	Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage	$\begin{split} V_{CB} &= 5.0 \text{ V}, \text{ I}_{C} = 10 \text{ mA} \\ V_{CE} &= 5.0 \text{ V}, \text{ I}_{C} = 50 \text{ mA} \\ \hline I_{C} &= 10 \text{ mA}, \text{ I}_{B} = 1.0 \text{ mA} \\ \hline I_{C} &= 50 \text{ mA}, \text{ I}_{B} = 5.0 \text{ mA} \\ \hline I_{C} &= 10 \text{ mA}, \text{ I}_{B} = 1.0 \text{ mA} \\ \hline I_{C} &= 50 \text{ mA}, \text{ I}_{B} = 5.0 \text{ mA} \\ \hline \end{array}$	40 40	0.2 0.5 1.0 1.0 6.0	V V
V _{CE(sat)} V _{BE(sat)} SMALL S C _{ob}	Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage IGNAL CHARACTERISTICS Output Capacitance Current Gain - Bandwidth Product	$\begin{split} V_{CB} &= 5.0 \text{ V}, \text{ I}_{C} = 10 \text{ mA} \\ V_{CE} &= 5.0 \text{ V}, \text{ I}_{C} = 50 \text{ mA} \\ \hline I_{C} &= 10 \text{ mA}, \text{ I}_{B} = 1.0 \text{ mA} \\ \hline I_{C} &= 50 \text{ mA}, \text{ I}_{B} = 5.0 \text{ mA} \\ \hline I_{C} &= 10 \text{ mA}, \text{ I}_{B} = 1.0 \text{ mA} \\ \hline I_{C} &= 50 \text{ mA}, \text{ I}_{B} = 5.0 \text{ mA} \\ \hline I_{C} &= 50 \text{ mA}, \text{ V}_{CB} = 10 \text{ V}, \text{ f} = 1.0 \text{ MHz} \\ \hline I_{C} &= 10 \text{ mA}, \text{ V}_{CE} = 10 \text{ V}, \text{ f} = 100 \text{ MHz} \end{split}$	40	0.2 0.5 1.0 1.0 6.0 400	V V V
$\begin{array}{c} h_{FE} \\ \hline V_{CE(sat)} \\ \hline V_{BE(sat)} \\ \hline \\ \hline \\ SMALL S \\ \hline \\ \hline \\ C_{ob} \\ \hline \\ f_T \\ \hline \\ \hline \\ h_{fe} \\ \hline \end{array}$	Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage	$\begin{split} V_{CE} &= 5.0 \text{ V}, \ I_C = 10 \text{ mA} \\ V_{CE} &= 5.0 \text{ V}, \ I_C = 50 \text{ mA} \\ \hline I_C &= 10 \text{ mA}, \ I_B = 1.0 \text{ mA} \\ \hline I_C &= 50 \text{ mA}, \ I_B = 5.0 \text{ mA} \\ \hline I_C &= 10 \text{ mA}, \ I_B = 1.0 \text{ mA} \\ \hline I_C &= 50 \text{ mA}, \ I_B = 5.0 \text{ mA} \\ \hline I_C &= 50 \text{ mA}, \ V_{CB} = 10 \text{ V}, \ f = 1.0 \text{ MHz} \\ \hline I_C &= 10 \text{ mA}, \ V_{CE} = 10 \text{ V}, \end{split}$	40 40	0.2 0.5 1.0 1.0 6.0	V V V

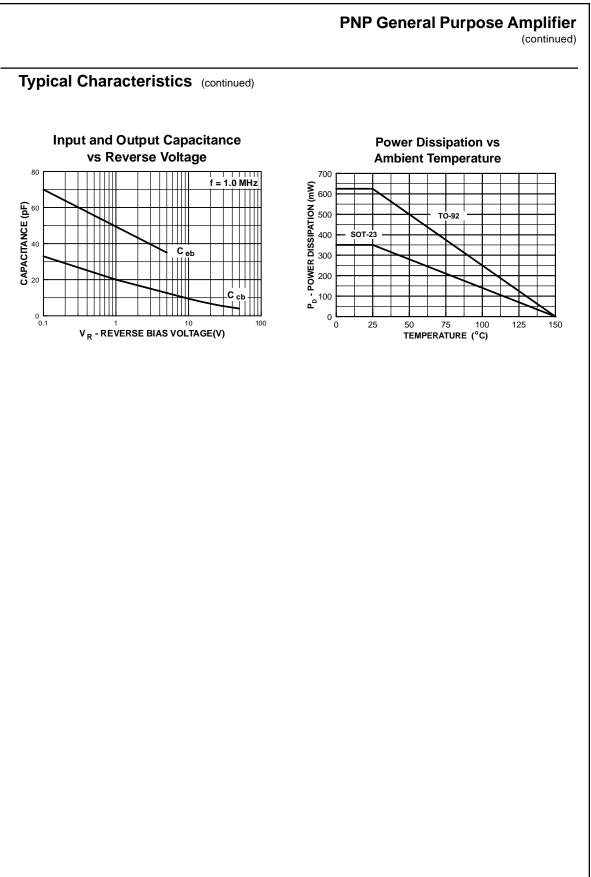
*Pulse Test: Pulse Width \pm 300 ms, Duty Cycle \pm 2.0%

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(continued) **Typical Characteristics Typical Pulsed Current Gain Collector-Emitter Saturation** vs Collector Current Voltage vs Collector Current / _ _ _ _ 5V / _{CE} = 5V β = 10 Π 125 °d 25 °C 25 0 125 °C °C ||| 0 L 0.1 0.0001 0.001 0.01 0.1 I c - COLLECTOR CURRENT (A) 10 100 I c - COLLECTOR CURRENT (mA) **Base-Emitter Saturation** Base-Emitter ON Voltage vs **Collector Current** Voltage vs Collector Current V BASE-EMITTER VOLTAGE (V) 0.0 0.0 0.1 0.0 0.1 0.1 0°C Ш Ш 25 °C 125 °C 125 °C β = 10 10 100 10 100 1 1 I c - COLLECTOR CURRENT (mA) Ic - COLLECTOR CURRENT (mA) **Collector-Emitter Breakdown Collector-Cutoff Current** vs Ambient Temperature Voltage with Resistance I_{ceo}- collector current (nA) 0 0 1 0 0 **Between Emitter-Base** V_{CB} = 100V 25 50 75 100 125 150 10 RESISTANCE (kΩ) 100 1000 T_A - AM BIENT TE MPE RATURE (°C)



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